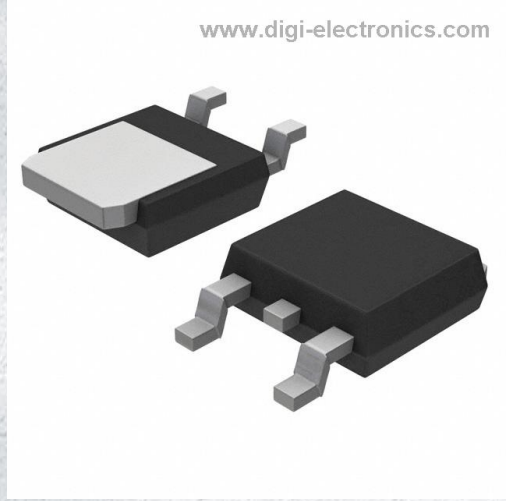
NTD32N06L Datasheet



DiGi Electronics Part Number	NTD32N06L-DG
Manufacturer	onsemi
Manufacturer Product Number	NTD32N06L
Description	MOSFET N-CH 60V 32A DPAK
Detailed Description	N-Channel 60 V 32A (Ta) 1.5W (Ta), 93.75W (Tj) Surface Mount DPAK

https://www.DiGi-Electronics.com

Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com

Purchase and inquiry

Manufacturer Product Number:	Manufacturer:
NTD32N06L	onsemi
Series:	Product Status:
-	Obsolete
FET Type:	Technology:
N-Channel	MOSFET (Metal Oxide)
Drain to Source Voltage (Vdss):	Current - Continuous Drain (Id) @ 25°C:
60 V	32A (Ta)
Drive Voltage (Max Rds On, Min Rds On):	Rds On (Max) @ Id, Vgs:
5V	28mOhm @ 16A, 5V
Vgs(th) (Max) @ Id:	Gate Charge (Qg) (Max) @ Vgs:
2V @ 250µA	50 nC @ 5 V
Vgs (Max):	Input Capacitance (Ciss) (Max) @ Vds:
±20V	1700 pF @ 25 V
FET Feature:	Power Dissipation (Max):
-	1.5W (Ta), 93.75W (Tj)
Operating Temperature:	Mounting Type:
-55°C ~ 175°C (TJ)	Surface Mount
Supplier Device Package:	Package / Case:
DPAK	TO-252-3, DPAK (2 Leads + Tab), SC-63
Base Product Number:	
NTD32	

Environmental & Export classification

RoHS Status:	Moisture Sensitivity Level (MSL):
RoHS non-compliant	1 (Unlimited)
REACH Status:	ECCN:
REACH Unaffected	EAR99
HTSUS:	
8541.29.0095	

ON Semiconductor

Is Now

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www.onsemi.com

NTD32N06L

Power MOSFET 32 Amps, 60 Volts

Logic Level, N-Channel DPAK

Designed for low voltage, high speed switching applications in power supplies, converters and power motor controls and bridge circuits.

Features

- Smaller Package than MTB30N06VL
- Lower $R_{DS(on)}$, $V_{DS(on)}$, and Total Gate Charge
- Lower and Tighter V_{SD}
- Lower Diode Reverse Recovery Time
- Lower Reverse Recovery Stored Charge
- Pb-Free Packages are Available

Typical Applications

- Power Supplies
- Converters
- Power Motor Controls
- Bridge Circuits

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Drain-to-Source Voltage	V_{DSS}	60	Vdc
Drain-to-Gate Voltage (R_{GS} = 10 MΩ)	V_{DGR}	60	Vdc
Gate-to-Source Voltage - Continuous - Non-Repetitive ($t_p \le 10$ ms)	V_{GS} V_{GS}	±20 ±30	Vdc
Drain Current - Continuous @ T_A = 25°C - Continuous @ T_A = 100°C - Single Pulse ($t_p \le 10$ μs)	I_D I_D I_{DM}	32 22 90	Adc Apk
Total Power Dissipation @ T_A = 25°C Derate above 25°C Total Power Dissipation @ T_A = 25°C (Note 1) Total Power Dissipation @ T_A = 25°C (Note 2)	P_D	93.75 0.625 2.88 1.5	W W/°C W W
Operating and Storage Temperature Range	T_J, T_{stg}	-55 to +175	°C
Single Pulse Drain-to-Source Avalanche Energy - Starting T_J = 25°C (Note 3) (V_{DD} = 50 Vdc, V_{GS} = 5 Vdc, L = 1.0 mH, $I_{L(pk)}$ = 25 A, V_{DS} = 60 Vdc, R_G = 25 Ω)	E_{AS}	313	mJ
Thermal Resistance - Junction-to-Case - Junction-to-Ambient (Note 1) - Junction-to-Ambient (Note 2)	 $R_{\theta JC}$ $R_{\theta JA}$ $R_{\theta JA}$	 1.6 52 100	°C/W
Maximum Lead Temperature for Soldering Purposes, 1/8 in from case for 10 seconds	T_L	260	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

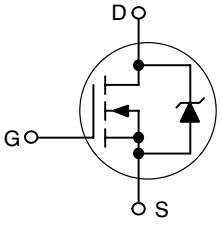
1. When surface mounted to FR4 board using 0.5 in pad size.
2. When surface mounted to FR4 board using minimum recommended pad size.
3. Repetitive rating; pulse width limited by maximum junction temperature.

ON Semiconductor®

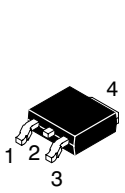
http://onsemi.com

V_{DSS}	$R_{DS(ON)}$ TYP	I_D MAX
60 V	23.7 mΩ	32 A

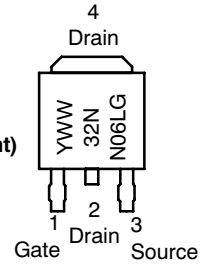
N-Channel

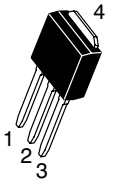


MARKING DIAGRAMS & PIN ASSIGNMENTS

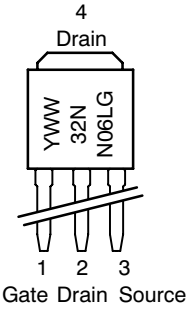


DPAK
CASE 369C
(Surface Mount)
STYLE 2





DPAK
CASE 369D
(Straight Lead)
STYLE 2



Y	= Year
WW	= Work Week
32N06L	= Device Code
G	= Pb-Free Package

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

June, 2007 - Rev. 5
Publication Order Number:
NTD32N06L/D

NTD32N06L

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Drain-to-Source Breakdown Voltage (Note 4) (V_{GS} = 0 Vdc, I_D = 250 μAdc) Temperature Coefficient (Positive)		$V_{(BR)DSS}$	 60 -	 70 62	 - -	Vdc mV/°C
Zero Gate Voltage Drain Current (V_{DS} = 60 Vdc, V_{GS} = 0 Vdc) (V_{DS} = 60 Vdc, V_{GS} = 0 Vdc, T_J = 150°C)		I_{DSS}	 - -	 - -	 1.0 10	μAdc
Gate-Body Leakage Current (V_{GS} = ±20 Vdc, V_{DS} = 0 Vdc)		I_{GSS}	-	-	±100	nAdc
ON CHARACTERISTICS (Note 4)						
Gate Threshold Voltage (Note 4) (V_{DS} = V_{GS}, I_D = 250 μAdc) Threshold Temperature Coefficient (Negative)		$V_{GS(th)}$	 1.0 -	 1.7 4.8	 2.0 -	Vdc mV/°C
Static Drain-to-Source On-Resistance (Note 4) (V_{GS} = 5 Vdc, I_D = 16 Adc)		$R_{DS(on)}$	 -	 23.7	 28	mΩ
Static Drain-to-Source On-Resistance (Note 4) (V_{GS} = 5 Vdc, I_D = 20 Adc) (V_{GS} = 5 Vdc, I_D = 32 Adc) (V_{GS} = 5 Vdc, I_D = 16 Adc, T_J = 150°C)		$V_{DS(on)}$	 - - -	 0.48 0.78 0.61	 0.67 - -	Vdc
Forward Transconductance (Note 4) (V_{DS} = 6 Vdc, I_D = 16 Adc)		g_{FS}	-	27	-	mhos
DYNAMIC CHARACTERISTICS						
Input Capacitance	(V_{DS} = 25 Vdc, V_{GS} = 0 Vdc, f = 1.0 MHz)	C_{iss}	-	1214	1700	pF
Output Capacitance		C_{oss}	-	343	480	
Transfer Capacitance		C_{rss}	-	87	180	
SWITCHING CHARACTERISTICS (Note 5)						
Turn-On Delay Time	(V_{DD} = 30 Vdc, I_D = 32 Adc, V_{GS} = 5 Vdc, R_G = 9.1 Ω) (Note 4)	$t_{d(on)}$	-	12.8	30	ns
Rise Time		t_r	-	221	450	
Turn-Off Delay Time		$t_{d(off)}$	-	37	80	
Fall Time		t_f	-	128	260	
Gate Charge	(V_{DS} = 48 Vdc, I_D = 32 Adc, V_{GS} = 5 Vdc) (Note 4)	Q_T	-	23	50	nC
		Q_1	-	4.5	-	
		Q_2	-	14	-	
SOURCE-DRAIN DIODE CHARACTERISTICS						
Forward On-Voltage	(I_S = 20 Adc, V_{GS} = 0 Vdc) (Note 4) (I_S = 32 Adc, V_{GS} = 0 Vdc) (Note 4) (I_S = 20 Adc, V_{GS} = 0 Vdc, T_J = 150°C)	V_{SD}	 - - -	 0.89 0.95 0.74	 1.0 - -	Vdc
Reverse Recovery Time	(I_S = 32 Adc, V_{GS} = 0 Vdc, dI_S/dt = 100 A/μs) (Note 4)	t_{rr}	-	56	-	ns
		t_a	-	31	-	
		t_b	-	25	-	
Reverse Recovery Stored Charge		Q_{RR}	-	0.093	-	μC

4. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.
5. Switching characteristics are independent of operating junction temperatures.

ORDERING INFORMATION

Device	Package	Shipping†
NTD32N06L	DPAK	75 Units / Rail
NTD32N06LG	DPAK (Pb-Free)	75 Units / Rail
NTD32N06L-1	DPAK (Straight Lead)	75 Units / Rail
NTD32N06L-1G	DPAK (Straight Lead) (Pb-Free)	75 Units / Rail
NTD32N06LT4	DPAK	2500 Units / Tape & Reel
NTD32N06LT4G	DPAK (Pb-Free)	2500 Units / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

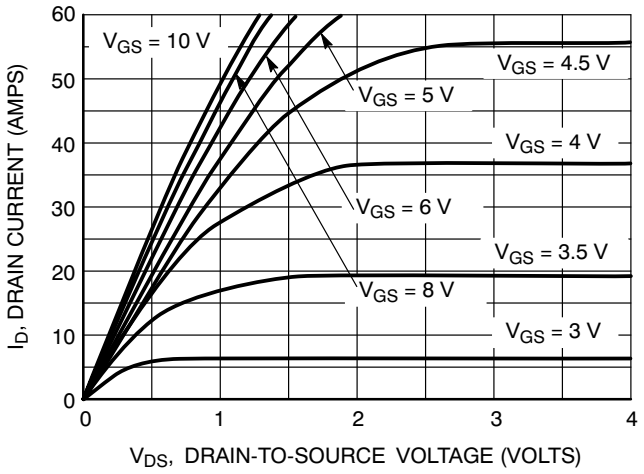


Figure 1. On-Region Characteristics

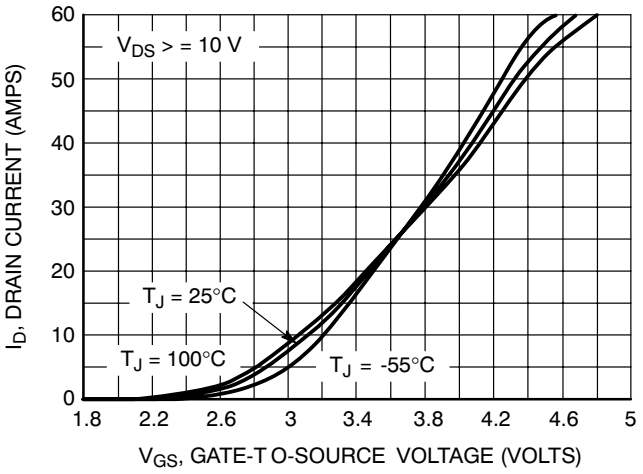


Figure 2. Transfer Characteristics

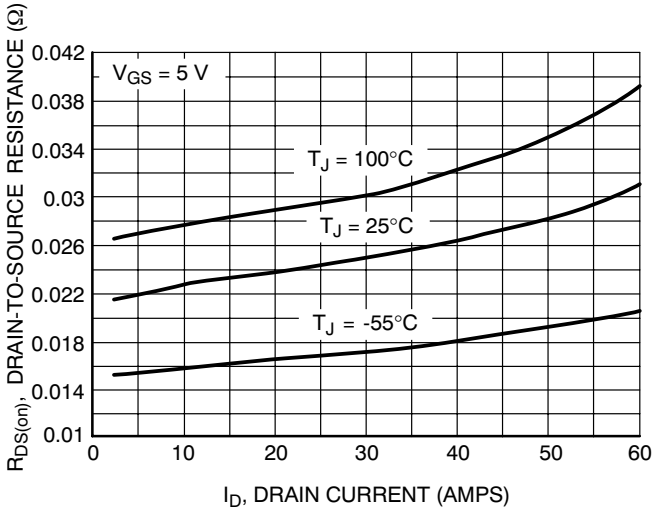


Figure 3. On-Resistance vs. Drain Current

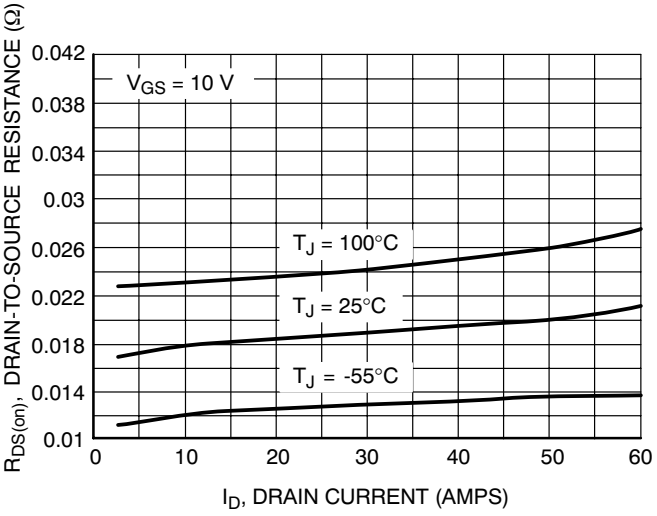


Figure 4. On-Resistance vs. Drain Current

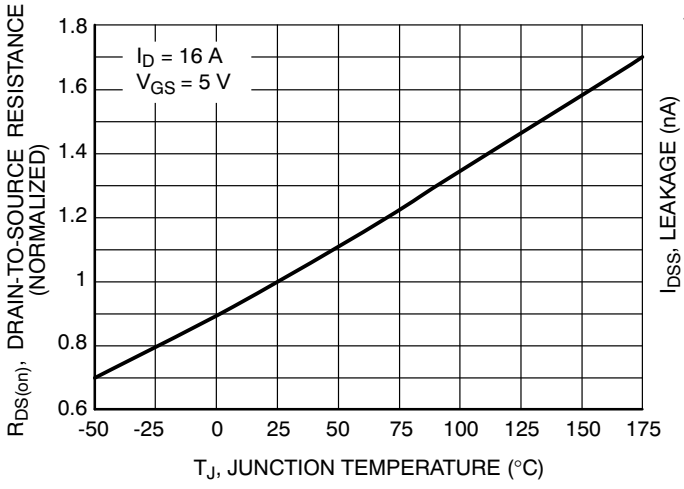


Figure 5. On-Resistance Variation with Temperature

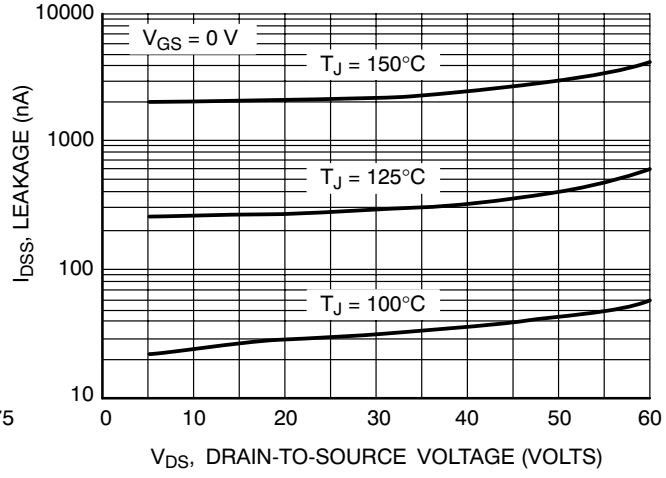


Figure 6. Drain-to-Source Leakage Current vs. Voltage

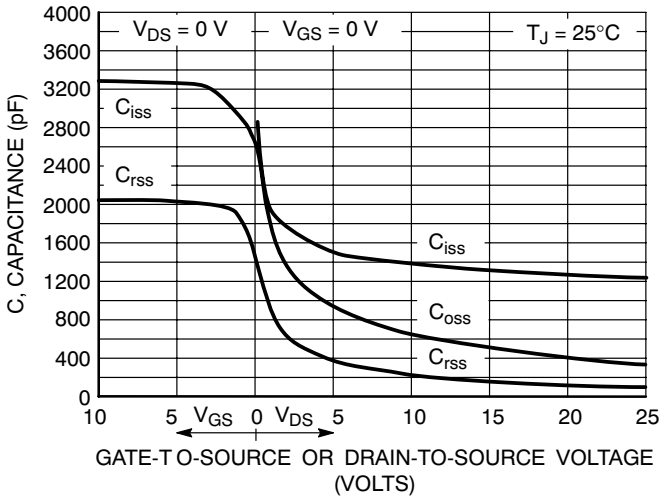


Figure 7. Capacitance Variation

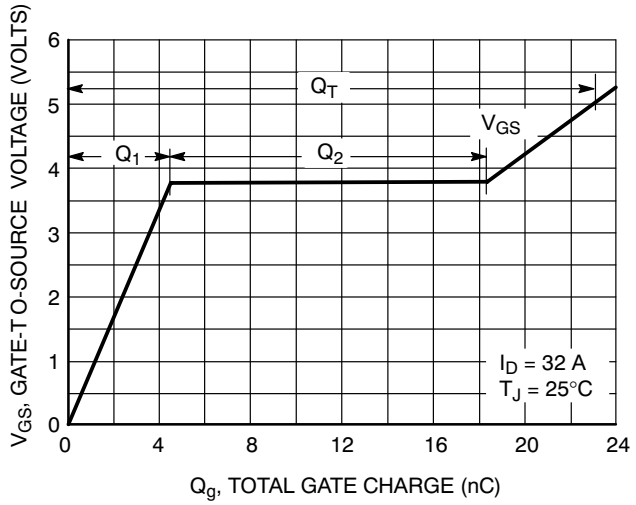


Figure 8. Gate-to-Source and Drain-to-Source Voltage vs. Total Charge

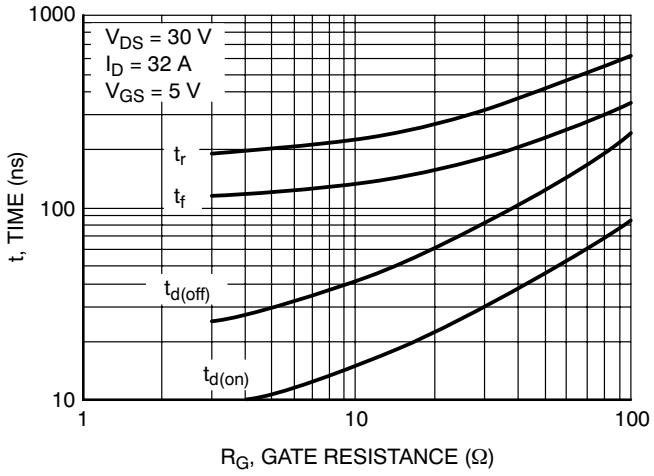


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

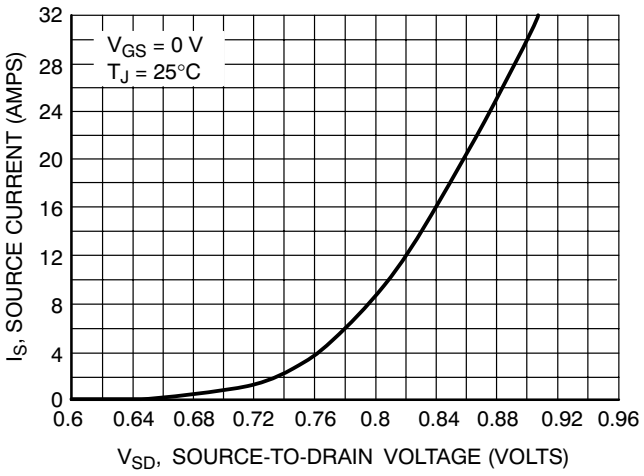


Figure 10. Diode Forward Voltage vs. Current

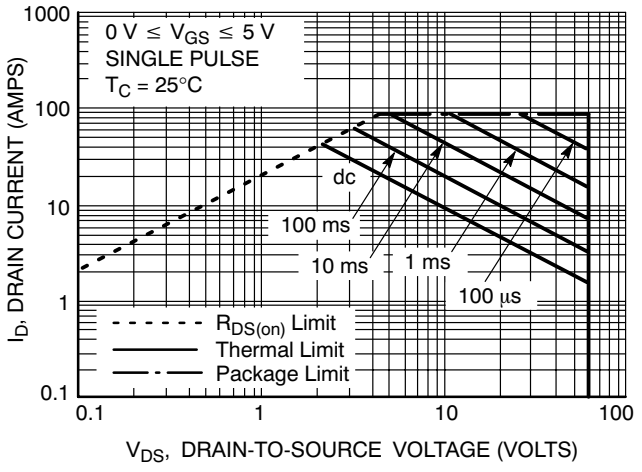


Figure 11. Maximum Rated Forward Biased Safe Operating Area

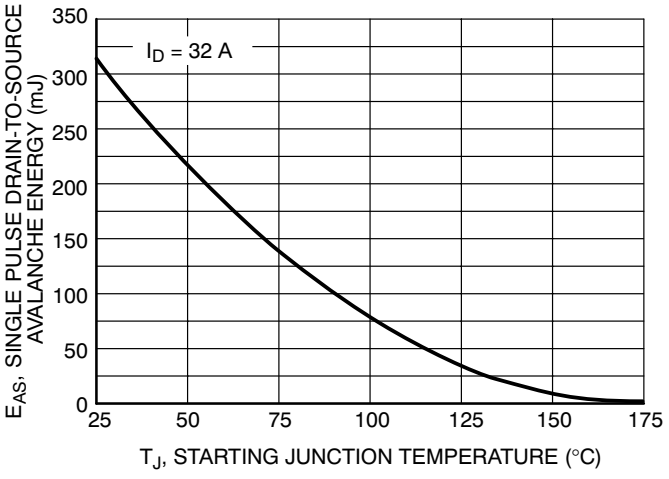


Figure 12. Maximum Avalanche Energy vs. Starting Junction Temperature

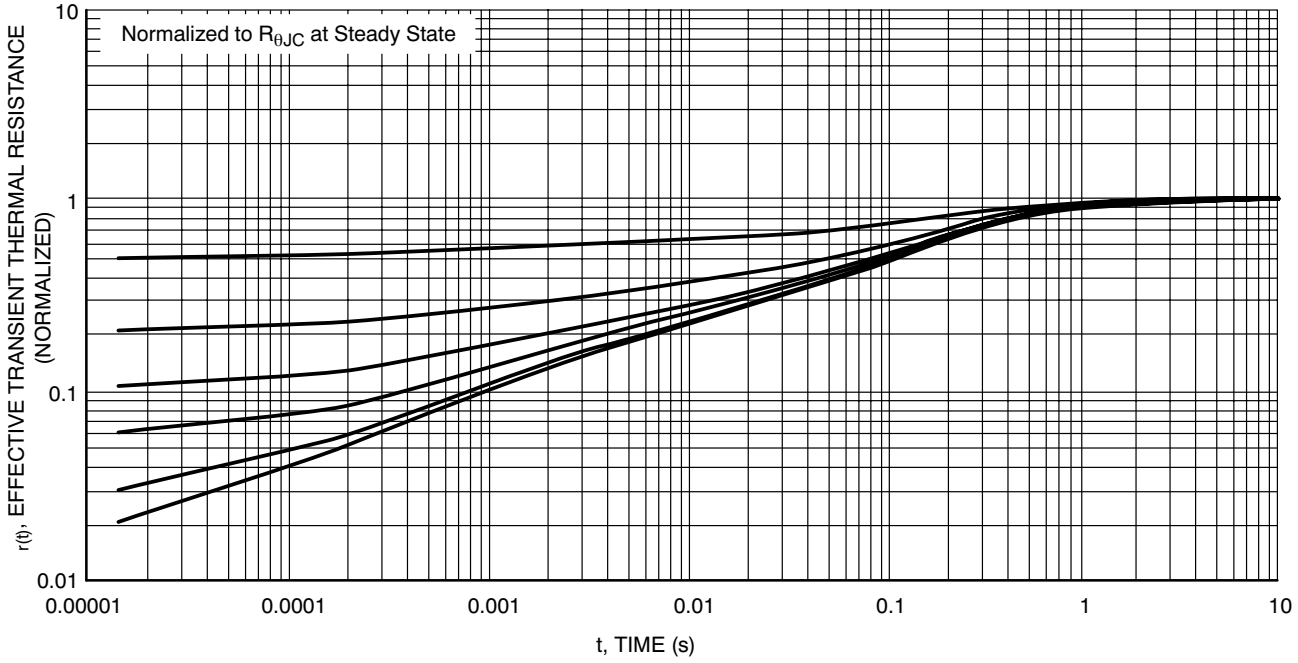


Figure 13. Thermal Response

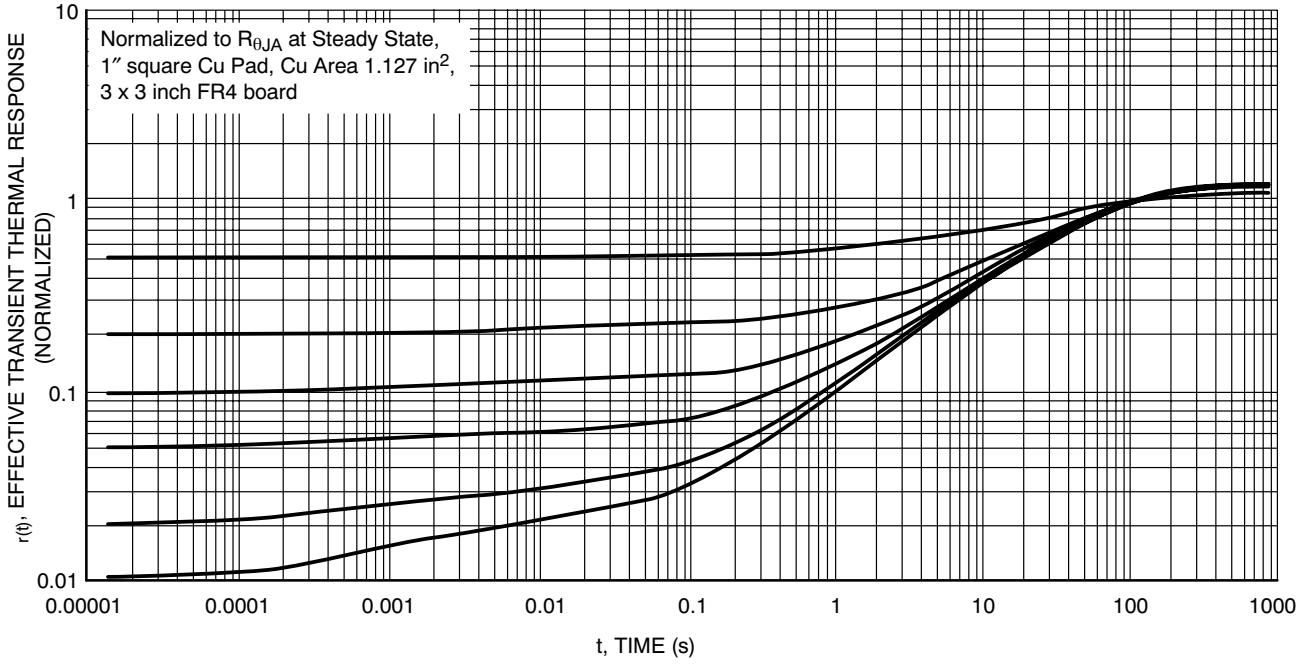
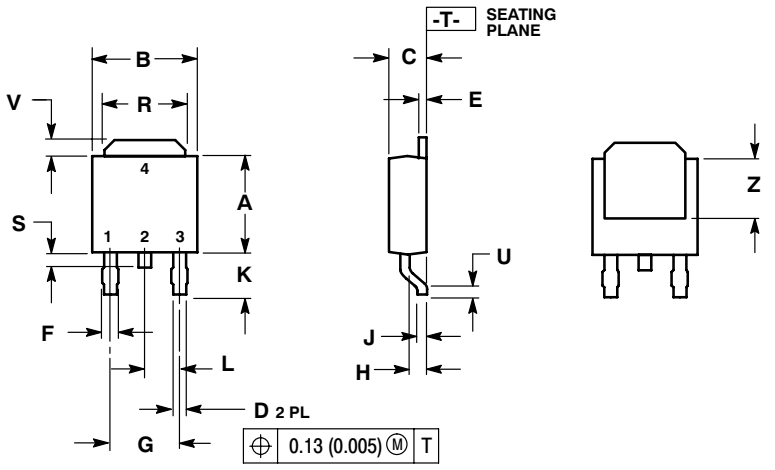


Figure 14. Thermal Response

NTD32N06L

PACKAGE DIMENSIONS

DPAK
CASE 369C-01
ISSUE O

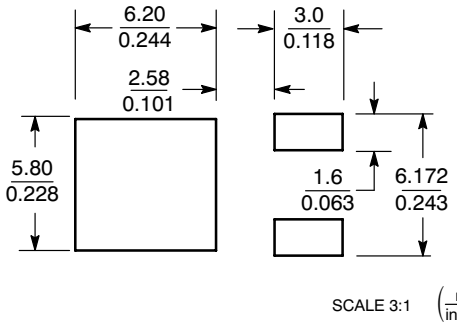


NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.235	0.245	5.97	6.22
B	0.250	0.265	6.35	6.73
C	0.086	0.094	2.19	2.38
D	0.027	0.035	0.69	0.88
E	0.018	0.023	0.46	0.58
F	0.037	0.045	0.94	1.14
G	0.180 BSC		4.58 BSC	
H	0.034	0.040	0.87	1.01
J	0.018	0.023	0.46	0.58
K	0.102	0.114	2.60	2.89
L	0.090 BSC		2.29 BSC	
R	0.180	0.215	4.57	5.45
S	0.025	0.040	0.63	1.01
U	0.020	---	0.51	---
V	0.035	0.050	0.89	1.27
Z	0.155	---	3.93	---

STYLE 2:
PIN 1. GATE
2. DRAIN
3. SOURCE
4. DRAIN

SOLDERING FOOTPRINT*

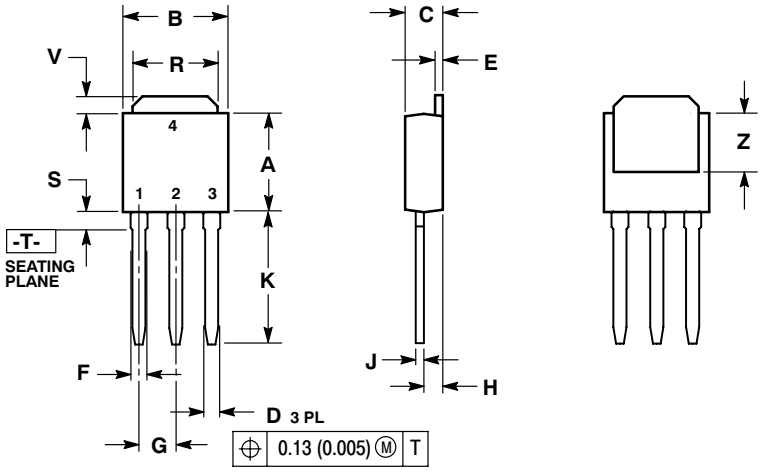


*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

NTD32N06L

PACKAGE DIMENSIONS

DPAK
CASE 369D-01
ISSUE B



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.235	0.245	5.97	6.35
B	0.250	0.265	6.35	6.73
C	0.086	0.094	2.19	2.38
D	0.027	0.035	0.69	0.88
E	0.018	0.023	0.46	0.58
F	0.037	0.045	0.94	1.14
G	0.090 BSC		2.29 BSC	
H	0.034	0.040	0.87	1.01
J	0.018	0.023	0.46	0.58
K	0.350	0.380	8.89	9.65
R	0.180	0.215	4.45	5.45
S	0.025	0.040	0.63	1.01
V	0.035	0.050	0.89	1.27
Z	0.155	---	3.93	---

STYLE 2:
PIN 1. GATE
2. DRAIN
3. SOURCE
4. DRAIN

PUBLICATION ORDERING INFORMATION

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Phone: 421 33 790 2910
Japan Customer Focus Center
Phone: 81-3-5773-3850

ON Semiconductor Website: **www.onsemi.com**

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For additional information, please contact your local Sales Representative

NTD32N06L/D

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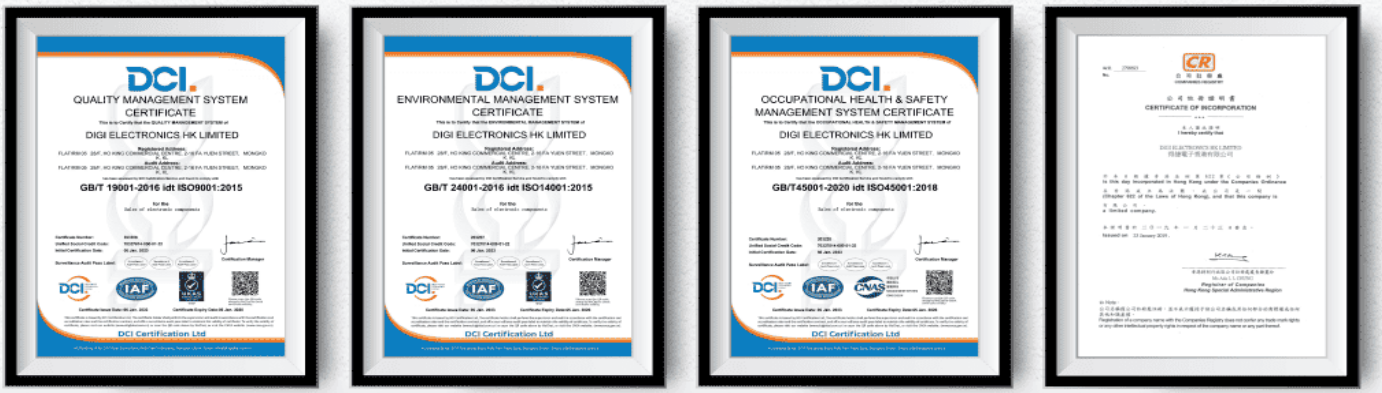

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RFQ Email: Info@DiGi-Electronics.com

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